

**ABSTRACT**

Provided is a method for manufacturing a semiconductor device, the method including a first mounting step of electrically connecting a first semiconductor element onto a substrate by means of a first wire, a lamination step of sticking a film-form adhesive on one side of a second semiconductor element having a larger area than the first semiconductor element, and a second mounting step of placing the second semiconductor element having the film-form adhesive stuck thereto, such that the film-form adhesive covers the first semiconductor element, mounting the film-form adhesive, and thereby embedding the first wire and the first semiconductor element in the film-form adhesive, in which the film-form adhesive has a shear viscosity at 80°C of 300 Pa·s or less as measured under the conditions of a frequency of 79.0 Hz, and in a case in which the shear viscosity at 80°C as measured under the conditions of a frequency of 0.1 Hz, 1.0 Hz, 10.0 Hz, and 79.0 Hz is designated as Y (Pa·s), the frequency is designated as X (Hz), and the relationship between X and Y is subjected to power approximation and is thereby represented by  $Y = aX^b$ , the gradient b is -0.67 or less.